

# 微纳光电子材料与器件工艺原理

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## Etching Part III: CMP and others

Xing Sheng 盛兴



Department of Electronic Engineering  
Tsinghua University

[xingsheng@tsinghua.edu.cn](mailto:xingsheng@tsinghua.edu.cn)

# Pattern Formation

Subtractive Process



Pattern transfer  
by etching

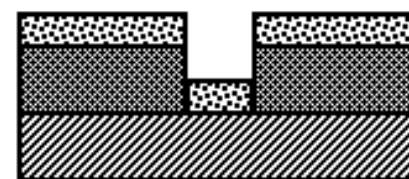
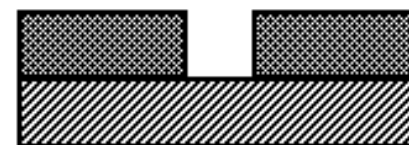
Photolithography

Etch

Deposit

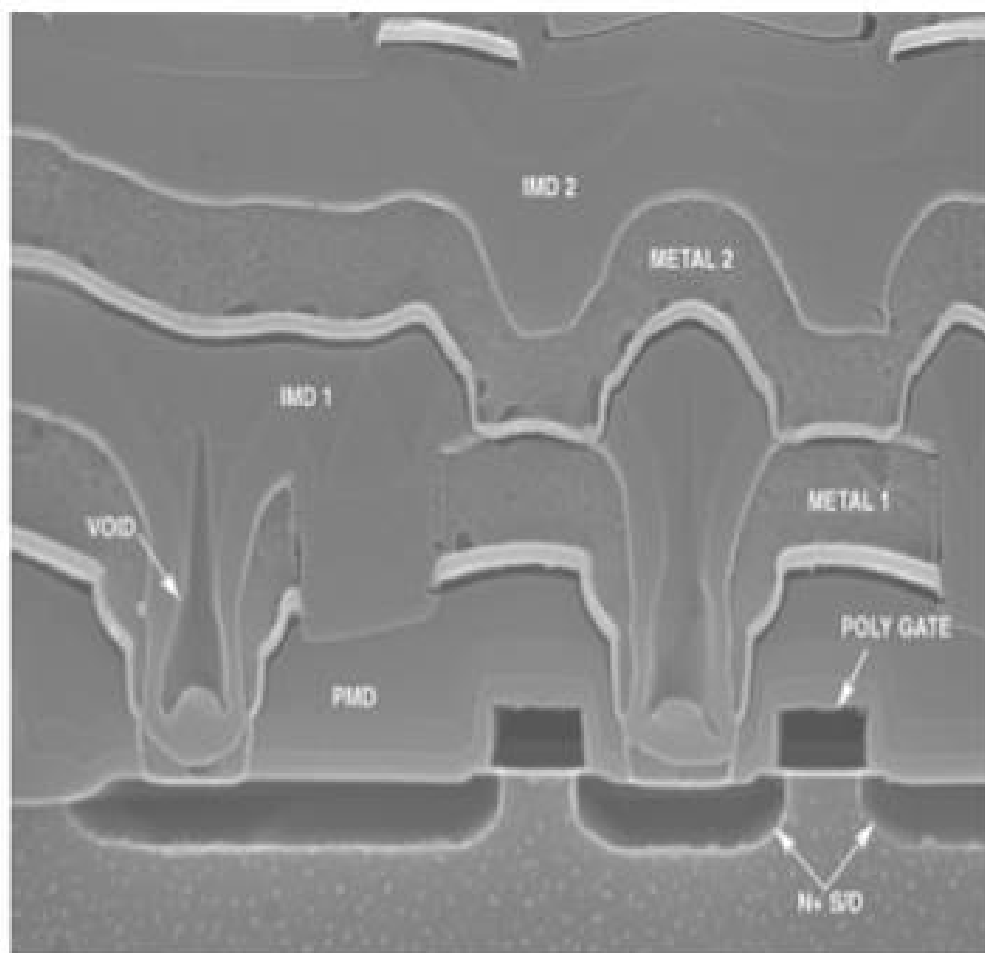
Strip Resist

Additive Process

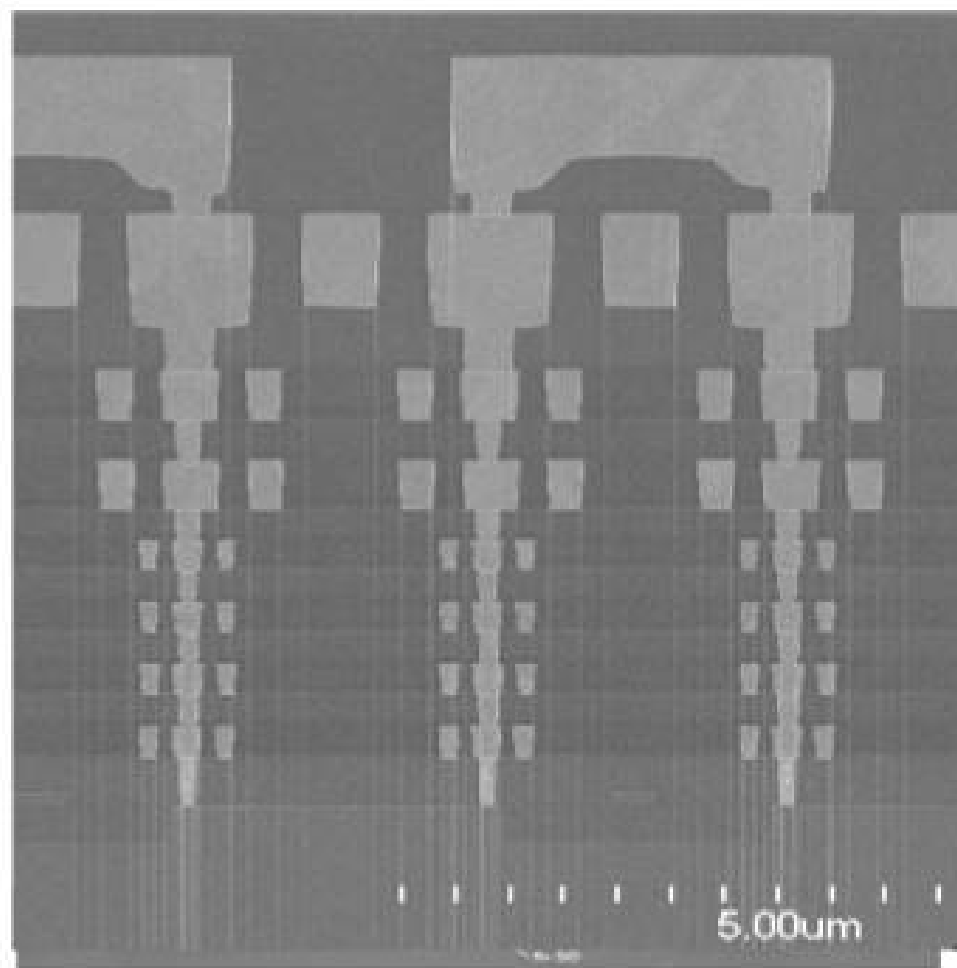


Pattern transfer  
by lift off

# Planar Layers are Desirable



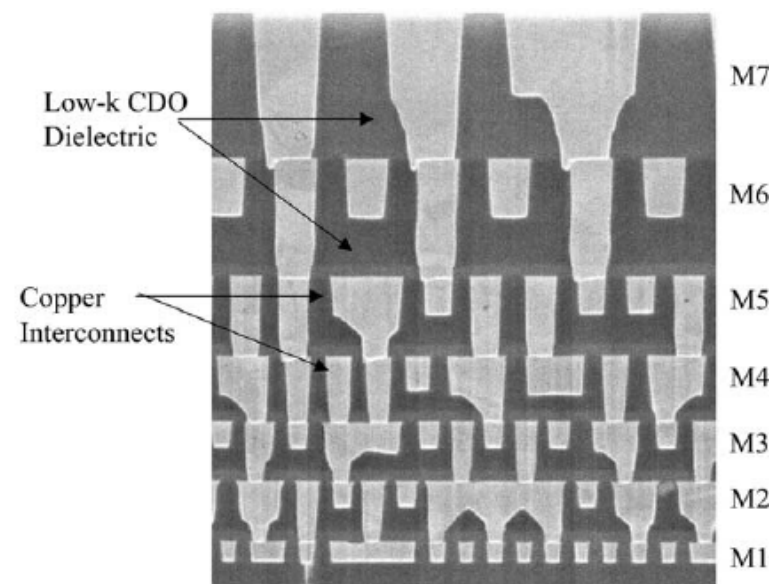
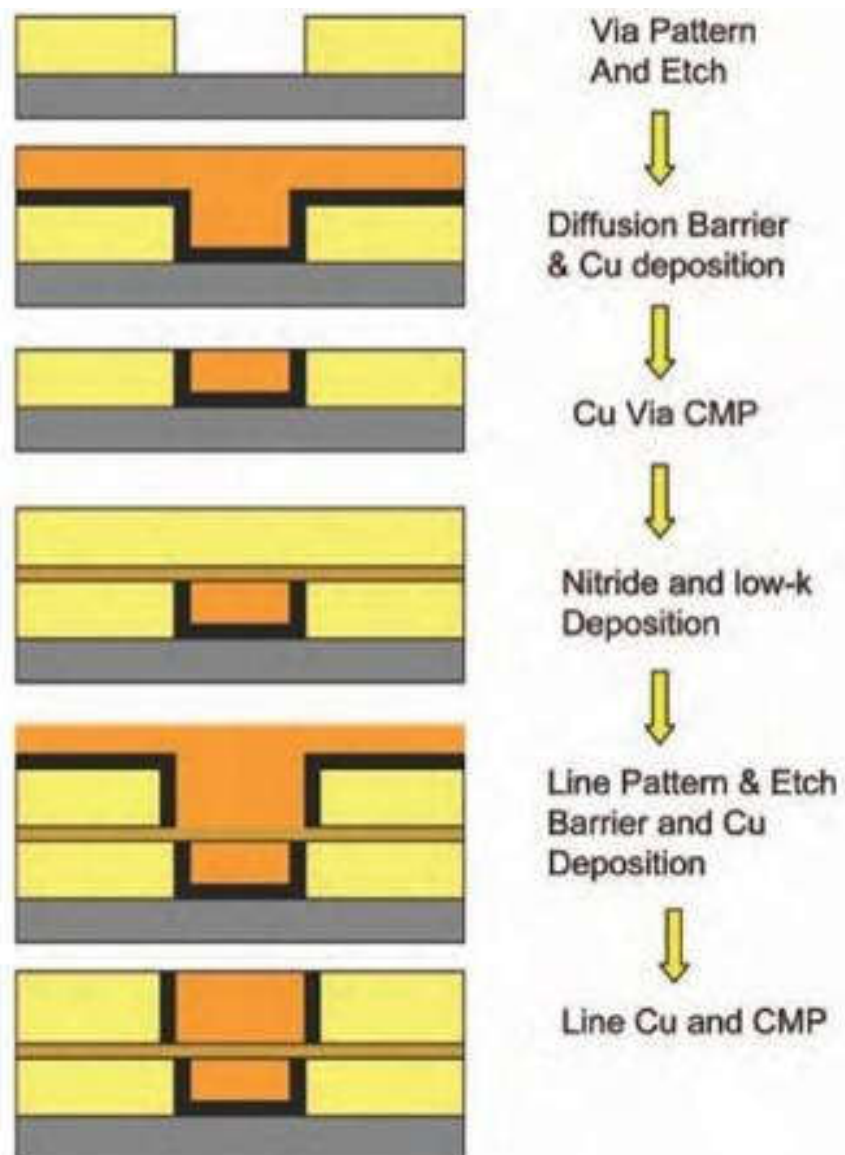
**non-planarized IC**



**planarized IC**

# Damascene Process

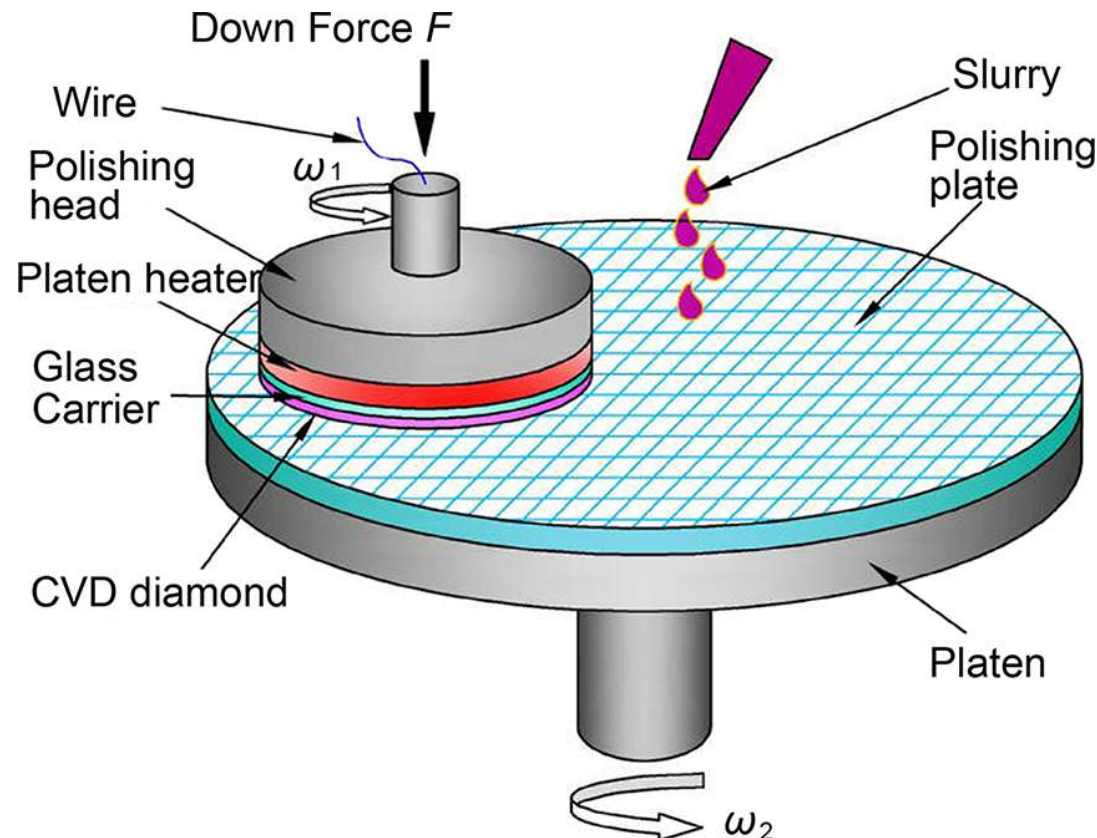
Cu  
SiO<sub>2</sub>



ancient art work

# CMP: Chemical Mechanical Polishing

- Chemical selectivity + Mechanical Planarization
- applied for Cu, W, SiO<sub>2</sub>, ...



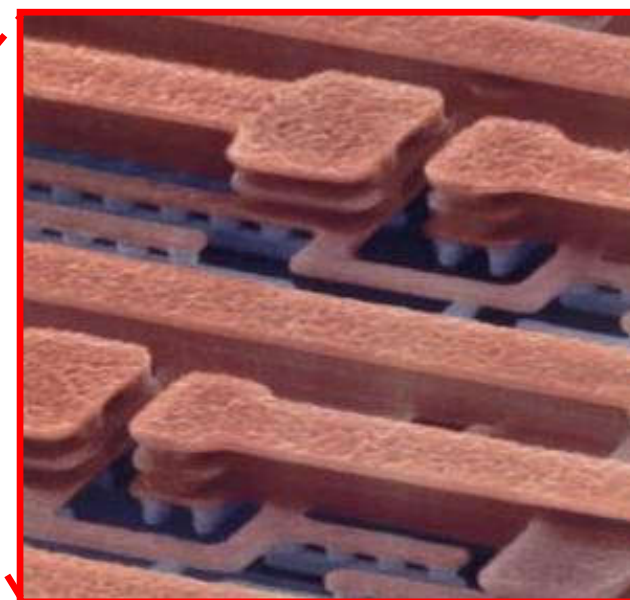
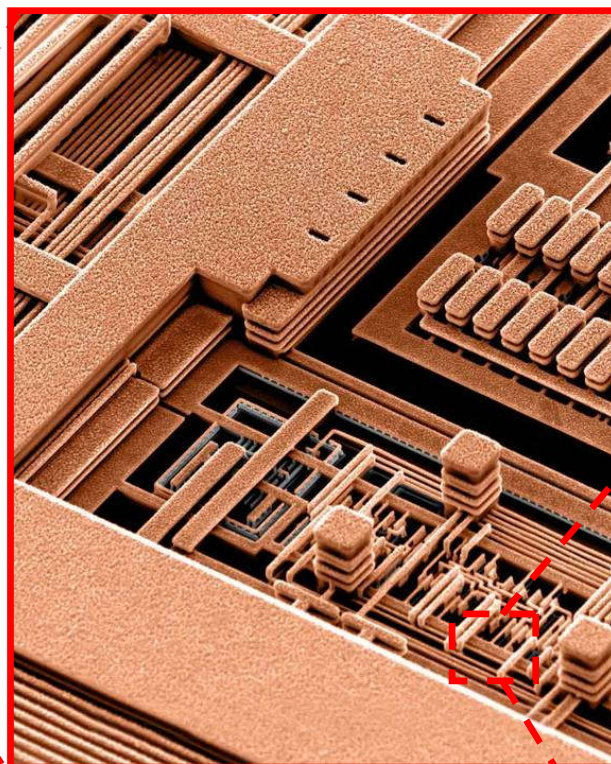
[Video](#)



# 3D IC



***Electroplating + CMP***  
***dirtiest process for the most advanced IC***



# Other Methods for Etching

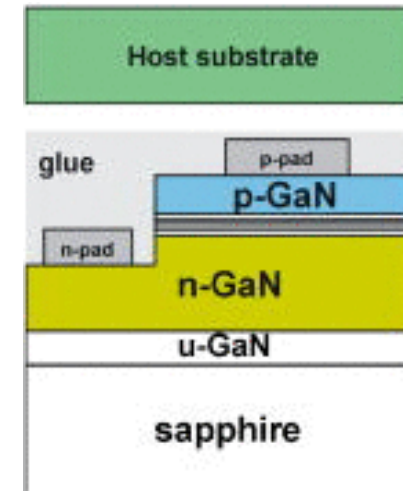
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- **Laser Lift-Off**
- **FIB: Focused Ion Beam**
- **Laser Milling**
- ...

# GaN Laser Liftoff

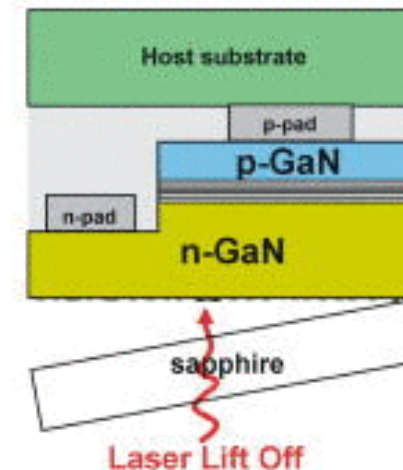
- GaN devices grown on sapphire

- ❑ low cost
- ❑ low thermal conductivity
- ❑ electrically insulating
- ❑ sapphire is very difficult to etch



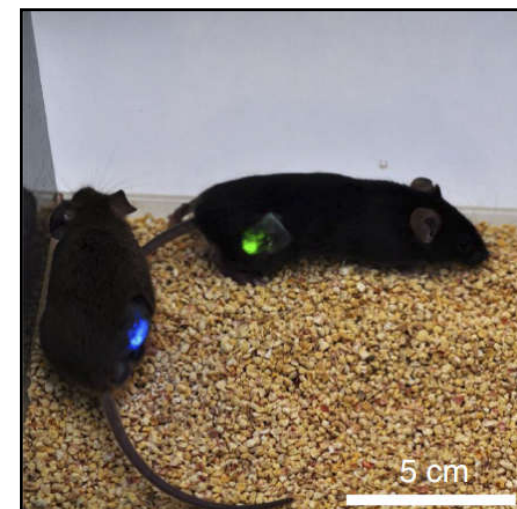
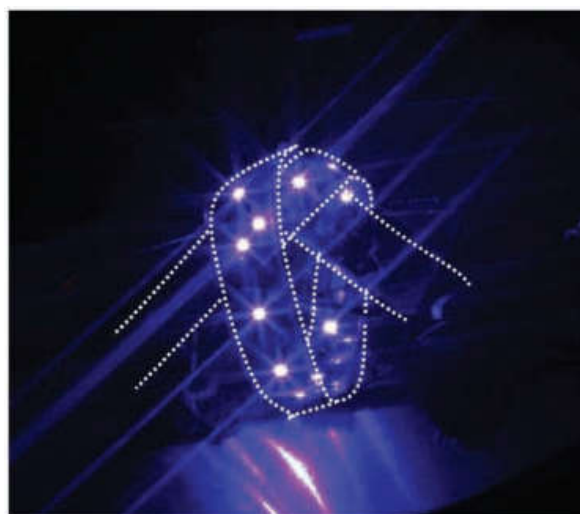
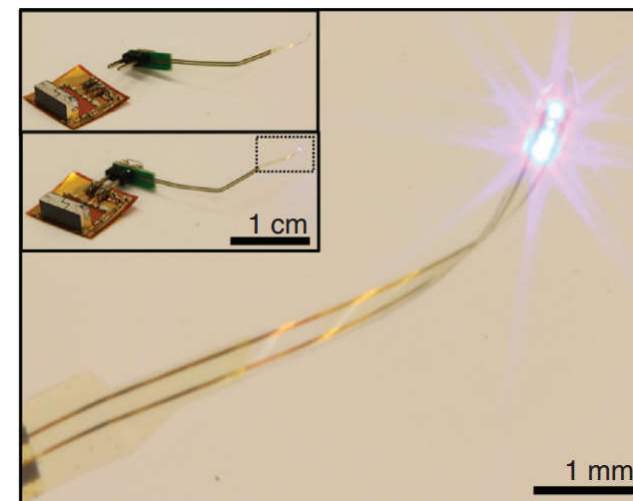
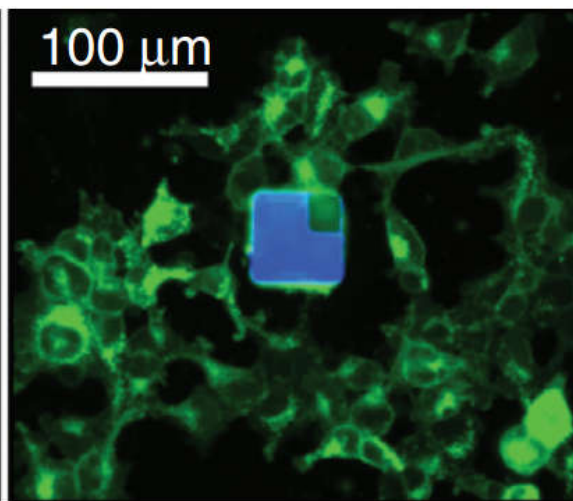
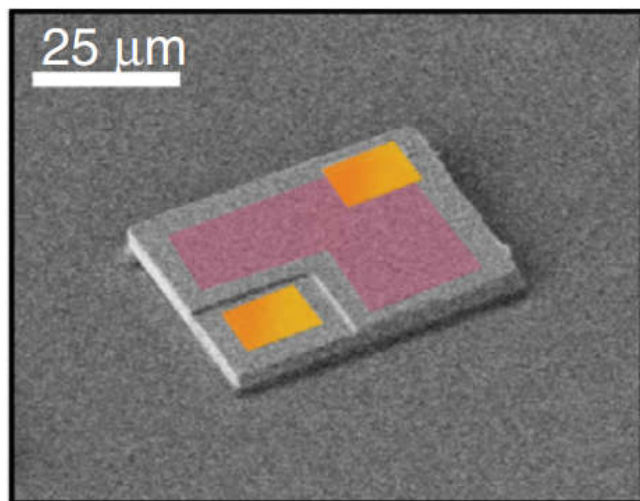
- Release by laser liftoff

- ❑ KrF excimer UV laser (248 nm)
- ❑  $\text{GaN} = \text{Ga} + \text{N}_2$  (gas)
- ❑ bonding onto new substrates

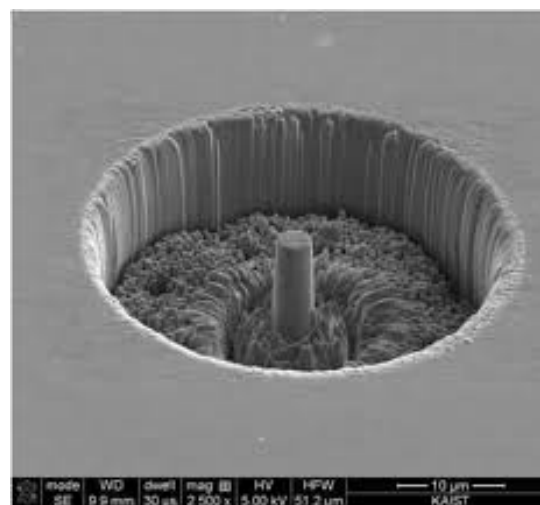
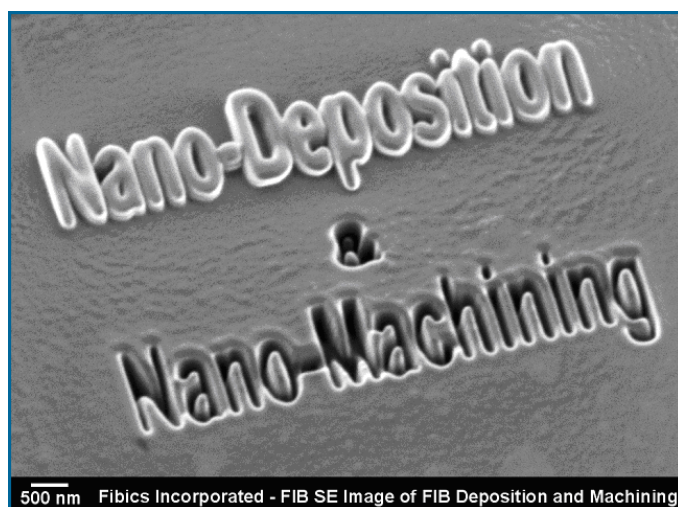
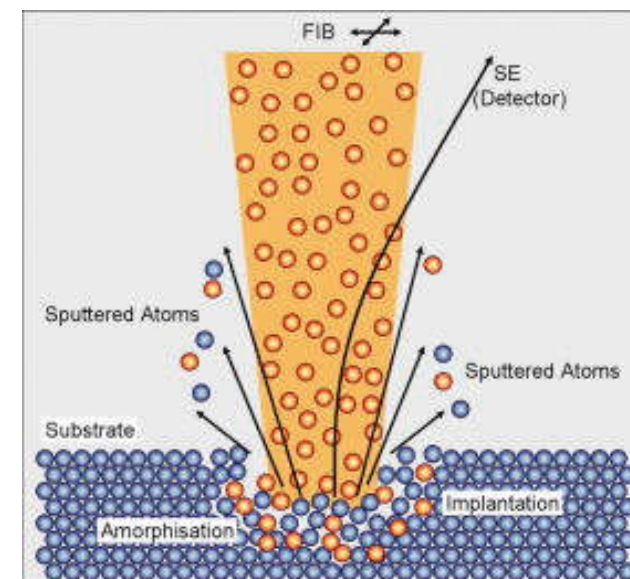
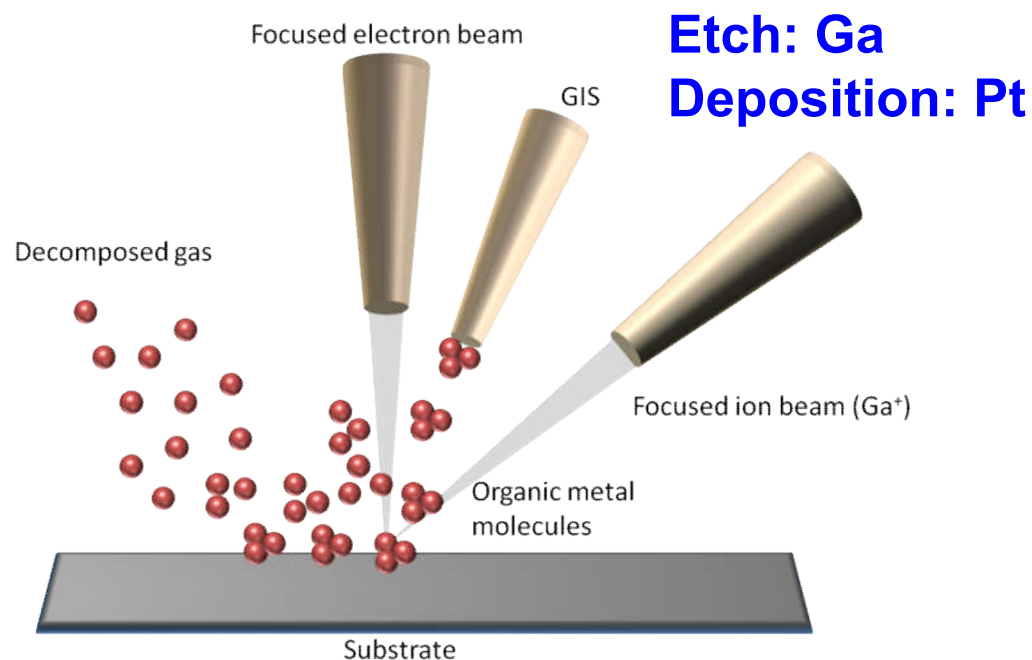




# Flexible GaN blue LEDs



# FIB: Focused Ion Beam



- nanostructures
- SEM/TEM sample preparation
- doping

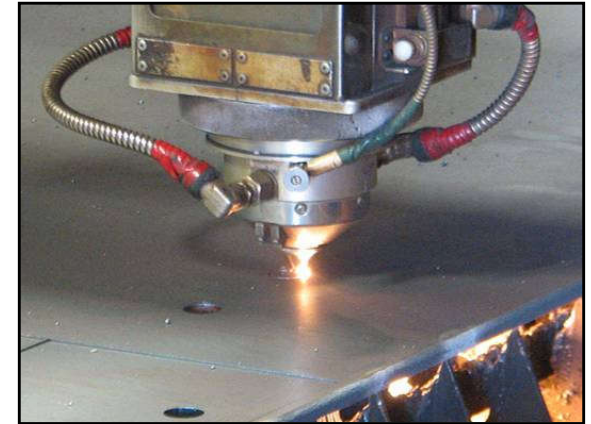
# Laser Milling

## ■ Types

- ❑ CO<sub>2</sub> laser 10 μm
- ❑ Near-IR laser 1064 nm
- ❑ UV laser 365 nm
- ❑ Excimer laser 248 nm, 193 nm
- ❑ ps/fs laser ...

## ■ Applications

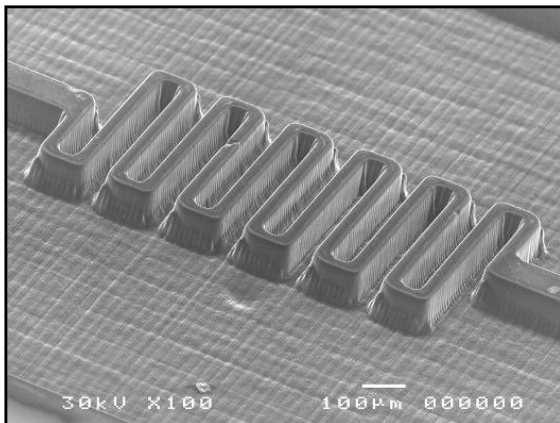
- ❑ die cut, PCB cut, ...



shorter wavelength  
shorter pulse



***better resolution***



***Thank you for your attention***